BIELE-013

## B.Tech. - VIEP - ELECTRONICS AND COMMUNICATION ENGINEERING (BTECVI)

00745

## Term-End Examination June, 2014

## BIELE-013 : DEVICE MODELLING FOR CIRCUIT SIMULATION

Time: 3 hours

Maximum Marks: 70

**Note:** Attempt any **seven** questions. All questions carry equal marks. Missing data may be suitably assumed. Calculators are permitted.

1. The transistor shown in the circuit of figure 1 has  $\beta = 100 \text{ and exhibits a } V_{BE} \text{ of } 0.7 \text{ V at i}_{C} = 1 \text{ mA}.$  Design the circuit (R<sub>C</sub> and R<sub>E</sub>) so that a current of 2 A flows through the collector and a voltage of + 5 V appears at the collector.

10

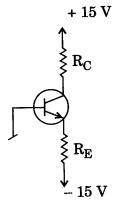


Figure 1

**2.** (a)

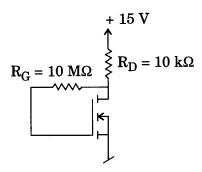


Figure 2

For the circuit shown in figure 2, the transistor has  $V_t$  = 1.5 V,  $K_n'$  (W/L) = 0.25 mA/V<sup>2</sup> and  $V_A$  = 50 V. Calculate  $I_D$ ,  $V_{DS}$  and  $V_{GS}$ .

5

- (b) An E-MOSFET with  $V_t$  = 0.7 V conducts a current  $i_D$  = 100  $\mu A$  when  $V_{GS}$  =  $V_{DS}$  = 1.2 V. Find  $i_D$  for  $V_{GS}$  = 1.5 V and  $V_{DS}$  = 3 V. Also calculate  $r_{DS}$  for small  $V_{DS}$  and  $V_{GS}$  = 3.2 V.
- **3.** With the help of a suitable example explain the principle and the objectives of circuit simulation. *10*
- **4.** Give the model statement in SPICE for the following:  $2\times5=10$ 
  - (i) Op-Amp
  - (ii) Diode
  - (iii) BJT
  - (iv) MOSFET
  - (v) FET

5.	Expla	do we understand by the term SPICE? in how will we carry out the AC and sient analysis of the circuit. $3+3\frac{1}{2}+$	$3\frac{1}{2}$
6.	detail	ss the small-signal model of a diode in with the help of suitable mathematical ssions.	10
7.	Expla MOSI	in in brief the various noise models of FETs.	10
8.		are the differences between LEVEL-1 and CL-2 large signal MOSFET models?	10
9.	Explain is brief the operation of following with the help of neat sketch:  5+5		
	(i)	$Heterojunction\ Bipolar\ Transistors\ (HBTs).$	
	(ii)	High-Electron Mobility Transistor (HEMT).	
10.	Write short notes on any <b>two</b> of the following: 5+5		
	(i)	Short-Channel Effects in MOSFETs	
	(ii)	MESFETs	
	(iii)	Principle of heterojunction device	